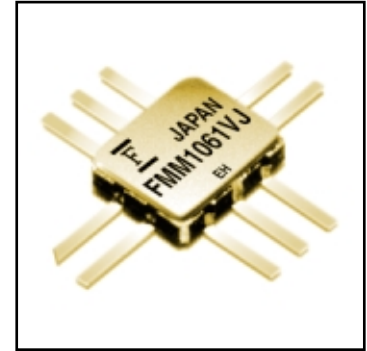


FEATURES

- Operation to 6.0 GHz
- Input Frequency divide by 4, OUT and $\overline{\text{OUT}}$
- -5V (or+5V) DC Single Power Supply
- External 50 ohm Load Driving Capability
- Small 10 pin Hermetic SMT-10 Package (VJ)
- Tape and Reel available

DESCRIPTION

The FMM1061VJ is a GaAs Microwave Static Frequency Divider designed for dividing an input signal by 4 over a frequency range from 2.0 to 6.0 GHz. This part is designed for Microwave Frequency Synthesizer and Phase-Locked Oscillator applications.



Fujitsu's stringent Quality Assurance Program assures the highest reliability and consistent performance.

ABSOLUTE MAXIMUM RATINGS (Ambient Temperature Ta=25°C)

Parameter	Symbol	Ratings	Unit
Supply Voltage	V _{SS}	-7.0 to 0	V
Input Voltage	V _{in}	V _{SS} to 0	V
Input Power	P _{in}	+13.0	dBm
Storage Temperature	T _{stg}	-55 to +125	°C
Power Dissipation	P _D	1.0	W

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Limit			Unit
		Min.	Typ.	Max.	
Supply Voltage	V _{SS}	-5.5	-5.0	-4.5	V
Ambient Temperature	T _a	-30	-	+70	°C

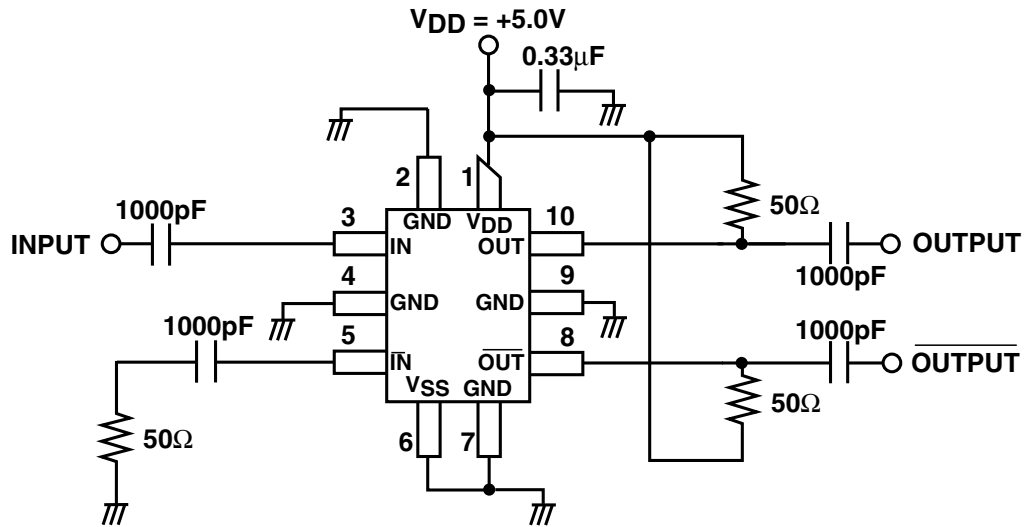
ELECTRICAL CHARACTERISTICS (Ambient Temperature Ta = 25°C, V_{SS} = -5.0V)

Parameter	Symbol	Condition	Limit			Unit
			Min.	Typ.	Max.	
Power Supply Current	I _{SS}		-	100	-	mA
Operating Frequency	f _{in}	P _{in} = 0~10dBm	2.0	-	6.0	GHz
Output Power	P _o		0	4	-	dBm

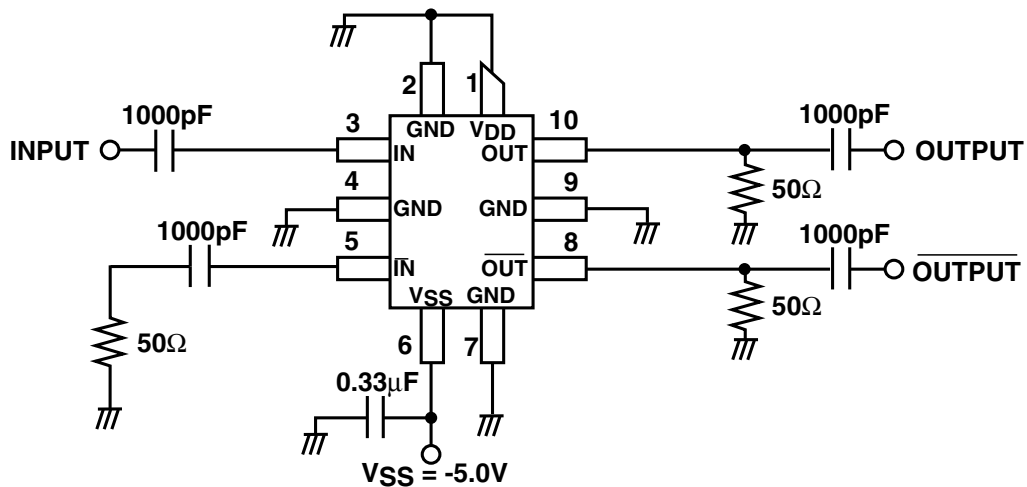
CASE STYLE: VJ

Test Circuit

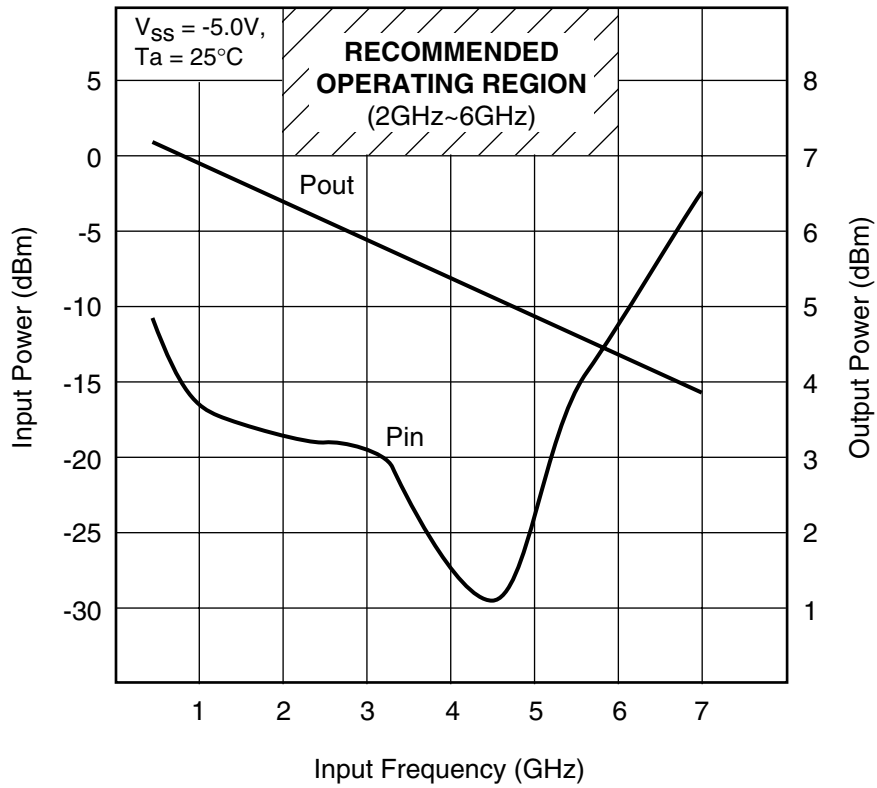
Positive Supply Voltage VDD = +5V Operation Circuit



Negative Supply Voltage VSS = -5V Operation Circuit



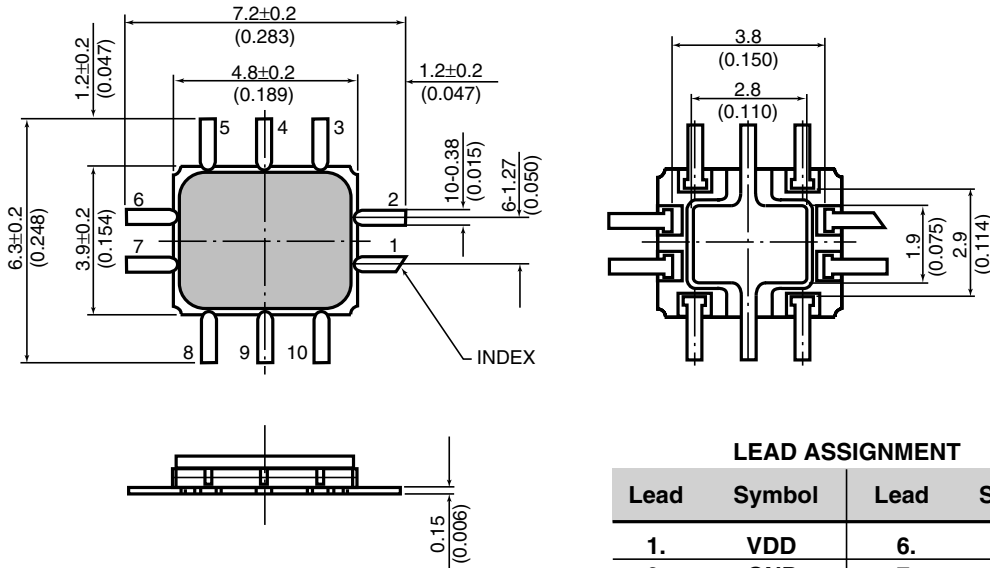
INPUT SENSITIVITY CHARACTERISTICS



FMM1061VJ

GaAs MMIC

Case Style "VJ"



Unit: mm(inches)

For further information please contact:

FUJITSU COMPOUND SEMICONDUCTOR, INC.

2355 Zanker Rd.

San Jose, CA 95131-1138, U.S.A.

Phone: (408) 232-9500

FAX: (408) 428-9111

www.fcsi.fujitsu.com

FUJITSU MICROELECTRONICS EUROPE, GmbH

Quantum Devices Division

Network House

Norreys Drive

Maidenhead, Berkshire SL6 4FJ

Phone:+44 (0)1628 504800

FAX:+44 (0)1628 504888

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- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.

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